

RELIABILITY REPORT

FOR

MAX2023ETX+

PLASTIC ENCAPSULATED DEVICES

September 9, 2009

# **MAXIM INTEGRATED PRODUCTS**

120 SAN GABRIEL DR. SUNNYVALE, CA 94086

Approved by	
Ken Wendel	
Quality Assurance	
Director, Reliability Engineering	



#### Conclusion

The MAX2023ETX+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim"s continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim"s quality and reliability standards.

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#### I. Device Description

A. General

The MAX2023 low-noise, high-linearity, direct upconversion/ downconversion quadrature modulator/demodulator is designed for single and multicarrier 1500MHz to 2300MHz DCS 1800/PCS 1900 EDGE, cdma2000®, WCDMA, and PHS/PAS base-station applications. Direct conversion architectures are advantageous since they significantly reduce transmitter or receiver cost, part count, and power consumption as compared to traditional IF-based double-conversion systems. In addition to offering excellent linearity and noise performance, the MAX2023 also yields a high level of component integration. This device includes two matched passive mixers for modulating or demodulating in-phase and quadrature signals, two LO mixer amplifier drivers, and an LO quadrature splitter. On-chip baluns are also integrated to allow for single-ended RF and LO connections. As an added feature, the baseband inputs have been matched to allow for direct interfacing to the transmit DAC, thereby eliminating the need for costly I/Q buffer amplifiers.

EDN China Innovation Award, Winner 2006
Direct-Conversion Transmitter Solution:
MAX2021MAX2023MAX2058MAX2059



#### II. Manufacturing Information

A. Description/Function: High-Dynamic-Range, Direct Up-/Downconversion 1500MHz to 2300MHz

Quadrature Mod/Demod

B. Process: G4

C. Number of Device Transistors:

D. Fabrication Location: Oregon

E. Assembly Location: China, ThailandF. Date of Initial Production: July 17, 2006

## III. Packaging Information

A. Package Type: 36-pin TQFN 6x6

B. Lead Frame: Copper

C. Lead Finish:

Die Attach:
Conductive Epoxy

E. Bondwire:

Gold (1 mil dia.)

F. Mold Material:

Epoxy with silica filler
Assembly Diagram:
#05-9000-2265

H. Flammability Rating:

Class UL94-V0

I. Classification of Moisture Sensitivity per

JEDEC standard J-STD-020-C

Level 1

J. Single Layer Theta Ja: 38°C/W
K. Single Layer Theta Jc: 1.4°C/W
L. Multi Layer Theta Ja: 28°C/W
M. Multi Layer Theta Jc: 1.4°C/W

#### IV. Die Information

A. Dimensions: 131 X 131 mils

B. Passivation: Si<sub>3</sub>N<sub>4</sub>
C. Interconnect: Au
D. Backside Metallization: None

E. Minimum Metal Width: 1.2 microns (as drawn) Metal 1, 2 & 3 5.6 microns (as

drawn) Metal 4

F. Minimum Metal Spacing: 1.6 microns (as drawn) Metal 1, 2 & 3, 4.2 microns (as

drawn) Metal 4

G. Bondpad Dimensions: 5 mil. Sq.
H. Isolation Dielectric: SiO<sub>2</sub>
I. Die Separation Method: Wafer Saw



#### V. Quality Assurance Information

A. Quality Assurance Contacts: Ken Wendel (Director, Reliability Engineering)

Bryan Preeshl (Managing Director of QA)

B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.

0.1% For all Visual Defects.

C. Observed Outgoing Defect Rate: < 50 ppm
D. Sampling Plan: Mil-Std-105D

# VI. Reliability Evaluation

#### A. Accelerated Life Test

The results of the 150°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate ( ) is calculated as follows:

$$\lambda = 1 \over \text{MTTF}$$
 = 1.83 (Chi square value for MTTF upper limit) (Chi square value for MTTF upper limit) (where 4340 x 48 x 2 (where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 9.98 \times 10^{-9}$$

 $\lambda$  = 9.98 F.I.T. (60% confidence level @ 25°C)

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at http://www.maxim-ic.com/qa/reliability/monitor. Cumulative monitor data for the G4 Process results in a FIT Rate of 0.02 @ 25C and 0.37 @ 55C (0.8 eV, 60% UCL)

#### B. Moisture Resistance Tests

The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

### C. E.S.D. and Latch-Up Testing

The CR37 die type has been found to have all pins able to withstand a HBM transient pulse of +/-2500 V per JEDEC JESD22-A114. Latch-Up testing has shown that this device withstands a current of +/-250 mA.



# **Table 1**Reliability Evaluation Test Results

# MAX2023ETX+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES		
Static Life Test (Note 1)						
`	Ta = 150°C Biased Time = 192 hrs.	DC Parameters & functionality	48	0		
Moisture Testing (Note 2)						
HAST	Ta = 130°C RH = 85% Biased Time = 96hrs.	DC Parameters & functionality	77	0		
Mechanical Stress (Note 2)						
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality	77	0		

Note 1: Life Test Data may represent plastic DIP qualification lots.

Note 2: Generic Package/Process data